

Electronic Acknowledgement Receipt

EFS ID:	8353578
Application Number:	10565621
International Application Number:	
Confirmation Number:	2319
Title of Invention:	Stacked structure and production method thereof
First Named Inventor/Applicant Name:	Hubert Moriceau
Customer Number:	90678
Filer:	Jasper W. Dockrey
Filer Authorized By:	
Attorney Docket Number:	9905-37 (BIF116044/US)
Receipt Date:	03-SEP-2010
Filing Date:	25-JUL-2006
Time Stamp:	17:05:42
Application Type:	U.S. National Stage under 35 USC 371

Payment information:

Submitted with Payment	no
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File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	NPL Documents	15-NF-OA-10-05-05.pdf	283265 dd115ac98b436cd51370eb67a21cd027e1d7fe	no	8

Warnings:

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2	NPL Documents	15-F-OA-05-03-06.pdf	400743 7a568d1b05a1ed2bde6c91e0557dca39927eecc	no	11
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3	NPL Documents	15-NF-OA-01-10-07.pdf	457128 6f99d257462c8a724488d01d3e18ca72db5662ee	no	12
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4	NPL Documents	15-F-OA-07-20-07.pdf	448778 9a2e086413a38141a11aebaa9a3d5c05a2c5a11	no	12
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5	NPL Documents	15-NF-OA-02-11-08.pdf	407731 6f1c5d518a0b0c3cbbba12cc0d851c9cce3cc3	no	11
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6	NPL Documents	15-F-OA-10-29-08.pdf	416204 212cc07587351e0d33b202bae7ba6ed3a6c5903e0d	no	11
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7	NPL Documents	15-NF-OA-6-25-09.pdf	273969 989998d2500fca7aadb358ac5e0815e02b560d4	no	8
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8	NPL Documents	16-OA-NF-9-24-04_1.PDF	271574 6c5e426497018c53767b7a7b07980c9a053a11c	no	7
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9	NPL Documents	16-OA-NF-6-6-05_1.PDF	235352 f15c505186cf7314813fd826ea3389a7fda2b7	no	6
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11	NPL Documents	16-OA-NF-5-17-06_1.PDF	215421 5188628c117094085Feb60453b01307d785db	no	5
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13	NPL Documents	16-OA-NF-2-6-08_1.PDF	979683 18f55c40b6eb4d3ce9789c578e17bfc9f98279cc	no	22
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14	NPL Documents	16-OA-F-10-17-08_1.PDF	1027800 c7c8fc78446007948c6ab8b52f8a6c61af95db7	no	23
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17	NPL Documents	34-OA-NF-3-26-08.pdf	299907 214db4f6aefcc08921a7048067ccc543f1c81a	no	9
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23	NPL Documents	Ono_et_al_Orientation_Dependence_of_Flaking_of_Ion_Irradiated.pdf	349210 99623b4efdc312021f4dbcc73b43b17c7940db	no	6
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24	NPL Documents	Paszti_E-Flaking_and_Wave-Like_Structure_On_Metallic_Glasses_Induced_By_MeV-Energy_Helium_Ions.pdf	811448 09b085a254d5e8b7676212c91a605e1073e081d	no	8
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25	NPL Documents	Picraux_S_Thomas_et_al_Ion_Impplantation_of_Surfaces.pdf	623657 c603c27d076d0112afedc7af63a3e24a18b10ea	no	9
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32	NPL Documents	Sah_Chih-Tang_et_al-Deactivation_of_the_Boron_Acceptor_in_Silicon_by_Hydrogen.pdf	300754 41129ff10202bfc77e07b5d6e02d4661927	no	3
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36	NPL Documents	Sioshansi_Piran_Ion_Beam_Modification_of_Materials.pdf	374037 5a3ab8cd80626d21d8b746ca7bf6ce073cd82	no	11
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39	NPL Documents	Stein_H_et_al-Infrared_Spectroscopy_of_Chemically.pdf	579683 fba72d3377162a6d86c997467332403ab2a8373	no	10
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44	NPL Documents	Tan_TY_et_al-On_Oxygen_Precipitation_Retardation-Recovery_Phenomena.pdf	563168 45522e8d8e7647f6b23b7d44d195570535cc219b6	no	11
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48	NPL Documents	Timoshenko_S_et_al-Analysis_of_Bi-Metal_Thermostats.pdf	1334964 2a0199513a988ad7f562a549c1cd79ec135d6a3	no	25
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53	NPL Documents	Van_de_Walle_C_et_al-Theory_of_Hydrogen-Vol-60.pdf	285435 e3d755913463ad757a8b4161c51d97bca8f05575	no	3
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60	NPL Documents	Weldon_et_al-Mechanism_of_Silicon_Exfoliation_Induced_by_Hydrogen.pdf	412773 196d17c2ae8298b3cd6f8a1b7c2d05181a5d405d	no	3
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If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.